

Description

Features

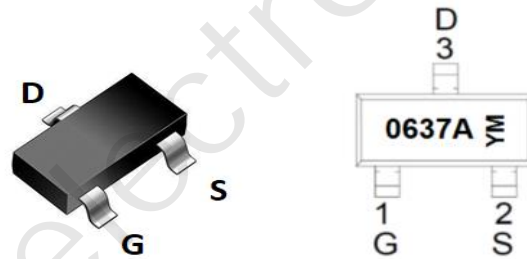
- 60V, 5.5A
 $R_{DS(ON)}$ Typ = 29mΩ @ $V_{GS} = 10V$
 $R_{DS(ON)}$ Typ = 35mΩ @ $V_{GS} = 4.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

| Device | Marking | Package | Outline | Reel Size | Reel (pcs) | Per Carton (pcs) |
|-------------|---------|-----------|---------|-----------|------------|------------------|
| CRMJTL0637A | 0637A | SOT-23-3L | TAPING | 7" | 3000 | 120000 |

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Value | Units |
|-----------------|--|---------------------------|-------|
| V_{DS} | Drain-to-Source Voltage | 60 | V |
| V_{GS} | Gate-to-Source Voltage | ±20 | V |
| I_D | Continuous Drain Current | $T_A = 25^\circ\text{C}$ | 5.5 |
| | | $T_A = 100^\circ\text{C}$ | 3.3 |
| I_{DM} | Pulsed Drain Current ⁽¹⁾ | 22 | A |
| P_D | Power Dissipation | $T_A = 25^\circ\text{C}$ | 2 |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient ⁽²⁾ | 62.5 | °C/W |
| T_J, T_{STG} | Junction & Storage Temperature Range | -55 to 150 | °C |

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

| Symbol | Parameter | Conditions | Min. | Typ. | Max. | Unit |
|--------|-----------|------------|------|------|------|------|
|--------|-----------|------------|------|------|------|------|

Off Characteristics

| | | | | | | |
|---------------|---------------------------------|---|----|---|-----------|---------------|
| $V_{(BR)DSS}$ | Drain-Source Breakdown Voltage | $I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$ | 60 | - | - | V |
| I_{DSS} | Zero Gate Voltage Drain Current | $V_{DS} = 60\text{V}, V_{GS} = 0\text{V}$ | - | - | 1.0 | μA |
| I_{GSS} | Gate-Body Leakage Current | $V_{DS} = 0\text{V}, V_{GS} = \pm 20\text{V}$ | - | - | ± 100 | nA |

On Characteristics

| | | | | | | |
|--------------|--|---|---|-----|------|------------------|
| $V_{GS(th)}$ | Gate Threshold Voltage | $V_{DS} = V_{GS}, I_D = 250\mu\text{A}$ | 1 | 1.6 | 2.2 | V |
| $R_{DS(ON)}$ | Static Drain-Source ON-Resistance ⁽³⁾ | $V_{GS} = 10\text{V}, I_D = 3\text{A}$ | - | 29 | 37.7 | $\text{m}\Omega$ |
| | | $V_{GS} = 4.5\text{V}, I_D = 2\text{A}$ | - | 35 | 45.5 | $\text{m}\Omega$ |

Dynamic Characteristics

| | | | | | | |
|-----------|------------------------------|---|---|------|---|----|
| C_{iss} | Input Capacitance | $V_{GS} = 0\text{V}, V_{DS} = 25\text{V},$ $f = 1\text{MHz}$ | - | 860 | - | pF |
| C_{oss} | Output Capacitance | | - | 62 | - | pF |
| C_{rss} | Reverse Transfer Capacitance | | - | 51 | - | pF |
| Q_g | Total Gate Charge | $V_{GS} = 0 \text{ to } 10\text{V}$ $V_{DS} = 30\text{V}, I_D = 5\text{A}$ | - | 20.3 | - | nC |
| Q_{gs} | Gate Source Charge | | - | 3.7 | - | nC |
| Q_{gd} | Gate Drain("Miller") Charge | | - | 5.3 | - | nC |

Switching Characteristics

| | | | | | | |
|--------------|--------------------|--|---|----|---|----|
| $t_{d(on)}$ | Turn-On DelayTime | $V_{GS} = 10\text{V}, V_{DD} = 30\text{V}$ $I_D = 5\text{A}, R_{GEN} = 1.8\Omega$ | - | 6 | - | ns |
| t_r | Turn-On Rise Time | | - | 6 | - | ns |
| $t_{d(off)}$ | Turn-Off DelayTime | | - | 19 | - | ns |
| t_f | Turn-Off Fall Time | | - | 3 | - | ns |

Drain-Source Diode Characteristics and Max Ratings

| | | | | | | |
|----------|--|---------------------------------------|---|---|-----|---|
| I_S | Maximum Continuous Drain to Source Diode Forward Current | | - | - | 5.5 | A |
| I_{SM} | Maximum Pulsed Drain to Source Diode Forward Current | | - | - | 22 | A |
| V_{SD} | Drain to Source Diode Forward Voltage | $V_{GS} = 0\text{V}, I_S = 3\text{A}$ | - | - | 1.2 | V |

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. $R_{\theta JA}$ is measured with the device mounted on a 1inch² pad of 2oz copper FR4 PCB
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform

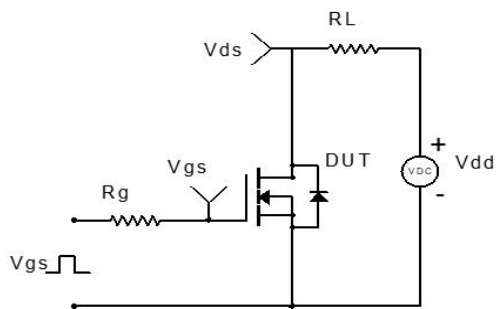


Figure 2: Resistive Switching Test Circuit & Waveform

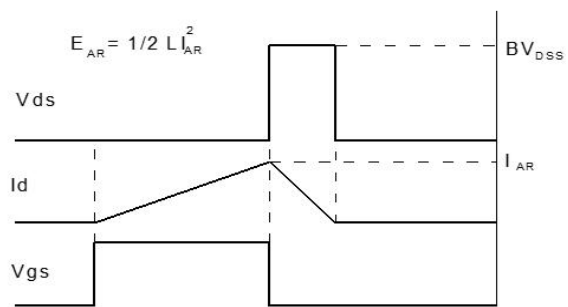
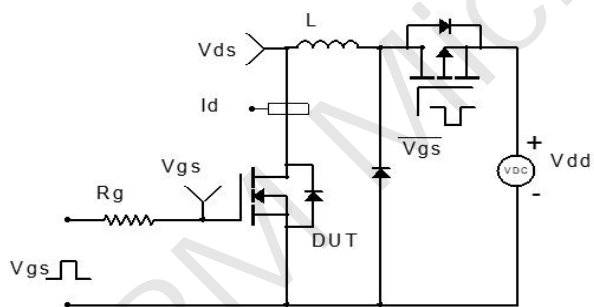
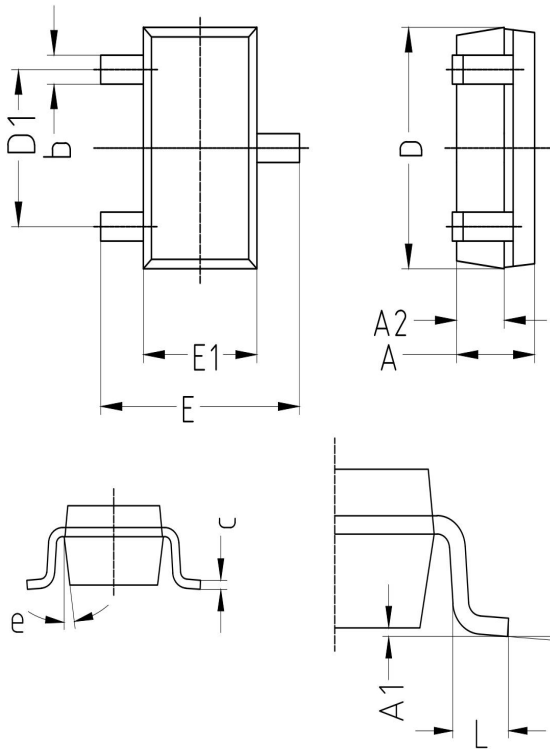


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(SOT-23-3L)



| COMMON DIMENSION (MM) | | | |
|-----------------------|-----------|-------|-------|
| PKG | SOT-23-3L | | |
| Symbol | MIN | MON | MAX |
| A | 1.080 | 1.100 | 1.120 |
| A1 | 0.010 | 0.060 | 0.150 |
| A2 | 0.640 | 0.670 | 0.700 |
| b | 0.325 | 0.350 | 0.375 |
| c | 0.125 | 0.135 | 0.150 |
| D | 2.92 | 2.930 | 2.980 |
| D1 | 1.875 | 1.900 | 1.925 |
| E | 2.650 | 2.800 | 2.950 |
| E1 | 1.580 | 1.600 | 1.670 |
| L | 0.300 | 0.450 | 0.600 |
| e | 8° | | |
| Q | 0° | 4° | 8° |

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